

RELIABILITY REPORT
FOR
MAX890LESA+
PLASTIC ENCAPSULATED DEVICES

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MAXIM INTEGRATED

160 RIO ROBLES
SAN JOSE, CA 95134

Approved by
Sokhom Chum
Quality Assurance
Reliability Engineer

Conclusion

The MAX890LESA+ successfully meets the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

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I. Device Description**A. General**

The MAX890L smart, low-voltage, P-channel, MOSFET power switch is intended for high-side load-switching applications. This switch operates with inputs from +2.7V to +5.5V, making it ideal for both +3V and +5V systems. Internal current-limiting circuitry protects the input supply against overload. Thermal-overload protection limits power dissipation and junction temperatures. The MAX890L's maximum current limit is 1.2A. The current limit through the switch is programmed with a resistor from SET to ground. The quiescent supply current is a low 10 μ A. When the switch is off, the supply current decreases to 0.1 μ A. The MAX890L is available in an 8-pin SO package.

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II. Manufacturing Information
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A. Description/Function:	1.2A, Current-Limited, High-Side P-Channel Switch with Thermal Shutdown
B. Process:	B12
C. Number of Device Transistors:	
D. Fabrication Location:	Oregon
E. Assembly Location:	Thailand, Philippines, or Malaysia
F. Date of Initial Production:	Pre 1997

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III. Packaging Information
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A. Package Type:	150 mil 8L SOIC
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1.3 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-1101-0090
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	1
J. Single Layer Theta Ja:	170°C/W
K. Single Layer Theta Jc:	40°C/W
L. Multi Layer Theta Ja:	128.4°C/W
M. Multi Layer Theta Jc:	36°C/W

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IV. Die Information
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A. Dimensions:	56 X 126 mils
B. Passivation:	Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al/0.5%Cu with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	1.2 microns (as drawn)
F. Minimum Metal Spacing:	1.2 microns (as drawn)
G. Bondpad Dimensions:	
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Richard Aburano (Manager, Reliability Engineering)
Don Lipps (Manager, Reliability Engineering)
Bryan Preeshl (Vice President of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 480 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 2.3 \times 10^{-9}$$

$$\lambda = 2.3 \text{ F.I.T. (60\% confidence level @ } 25^{\circ}\text{C)}$$

The following failure rate represents data collected from Maxim Integrated's reliability monitor program. Maxim Integrated performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maximintegrated.com/qa/reliability/monitor>. Cumulative monitor data for the B12 Process results in a FIT Rate of 0.02 @ 25C and 0.33 @ 55C (0.8 eV, 60% UCL)

B. E.S.D. and Latch-Up Testing (lot JX3BEQ001I, D/C 1048)

The PX82-1 die type has been found to have all pins able to withstand a transient pulse of:

ESD-HBM:	+/- 2500V per JEDEC JESD22-A114
ESD-CDM:	+/- 750V per JEDEC JESD22-C101

Latch-Up testing has shown that this device withstands a current of +/- 100mA and overvoltage per JEDEC JESD78.

Table 1
Reliability Evaluation Test Results

MAX890LESA+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (Note 1)	Ta = 135°C	DC Parameters & functionality	80	0	NX3BCA112BQ, D/C 0210
	Biased		80	0	IX3BB3156AQ, D/C 0011
	Time = 192 hrs.		80	0	NLCBFQ002A, D/C 9814
			80	0	NLCBGU001A, D/C 9801
			80	0	NNUEDQ002B, D/C 9845
			80	0	NLCBHB024B, D/C 9752

Note 1: Life Test Data may represent plastic DIP qualification lots.